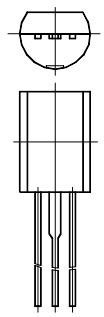
2SD667, 2SD667A TRANSISTOR (NPN)

TO-92MOD



1. EMITTER
2. COLLECTOR
3. BASE

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FEATURES

Power dissipation

$P_{CM:}$ 0.9 W (Tamb=25℃)

Collector current

$I_{CM:}$ 1 A

Collector-base voltage

$V_{(BR)CBO}$: 120 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0		120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	2SD6677	80			V
			2SD667A	100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0		5			V
Collector cut-off current	I_{CBO}	V_{CB}=100V, I_E=0				10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V, I_C=0				10	μA
DC current gain	$h_{FE(1)}$	V_{CE}=5V, I_C=150mA	2SD667	60		320	
			2SD667A	60		200	
	$h_{FE(2)}$	V_{CE}=5V, I_C=500mA		30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA				1	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C=150mA				1.5	V
Transition frequency	f_T	V_{CE}=5V, I_C=150mA			140		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz			12		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank		B	C	D
Range	2SD667	60-120	100-200	160-320
	2SD667A	60-120	100-200	